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2838

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Atty. Docket: KAGADEI=1

In re Application of:	)	Conf. No.: 6897
	)	
V. KAGADEI et al.	)	Art Unit: 2838
	)	
Appln. No.: 10/086,621	)	Examiner:
	)	
Filed: March 4, 2002	)	Washington, D.C.
	)	
For: A METHOD AND APPARATUS	)	November 4, 2002
FOR PRODUCING ATOMIC...	)	

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CORRECTED PTO 1449

Honorable Commissioner for Patents  
Washington, D.C. 20231

Sir:

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Regarding with the Information Disclosure Statement  
filed June 18, 2002, in the above-identified case, there were  
errors in some the references listed.

Citations AC, AK, AO, AR AT and AU have errors.  
Please find attached a corrected substitute for form PTO  
1449A, i.e. PTO/SB/57.

Respectfully submitted,  
BROWDY AND NEIMARK, P.L.L.C.  
Attorneys for Applicant(s)

By

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G:\BN\C\cohn\Kagadei\corrected 1449 4NOV.02.doc

Substitute for form 1449A/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2

of 3

## Complete if Known

Application Number	10/086,621
Filing Date	March 4, 2002
First Named Inventor	V. KAGADEI et al.
Group Art Unit	
Examiner Name	
Attorney Docket Number	KAGADEI=1

## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
	AC	LEONE, "Kinetic-Energy-Enhanced Neutral Etching", <u>Jpn. J. Appl. Phys.</u> , (1995), vol. 34, No. 4B, pages 2073-2082	
	AD	ORLIKOVSKY, "Plasma Processes in Micro- and Nanoelectronics Part 1. Reactive Etching", <u>Microelectronics</u> , (1999), vol. 28, No. 5, Pages 344-362	XXX
	AE	ROUSSEAU et al., "Pulsed microwave discharge: a very efficient H atom source", <u>J. Phys. D: Phys.</u> , (1994), vol. 27, pages 2439-2441	
	AF	POPOV et al., "Electron cyclotron resonance plasma stream source for plasma enhanced chemical vapor deposition", <u>J. Vac. Sci. Technol. A</u> , (1989), vol. 7, No. 3, pages 914-917	
	AG	KROON, "Removal of Oxygen for the Si(100) Surface in a DC Hydrogen Plasma", <u>Jpn. J. Appl. Phys.</u> , (1997), vol. 36, pages 5068-5071	
	AH	BARDOS et al., "Linear arc discharge source for large area plasma processing", <u>Appl. Phys. Lett.</u> , (1997), vol. 70, No. 5, pages 577-579	
	AI	LIPPERT et al., "Soft Cleaning by <i>In Vacuo</i> Ultraviolet Radiation Combined with Molecular Hydrogen Gas before Molecular Beam Epitaxial Layer Growth", <u>J. Electrochem. Soc.</u> , (1995), vol. 142, No. 1, pages 191-195	
	AJ	SUGAYA et al., "Low-Temperature Cleaning of GaAs Substrate by Atomic Hydrogen Irradiation", <u>Japanese Journal of Applied Physics</u> , (1991), vol. 30, No. 3A, pages L402-L404	
	AK	WOLAN et al., "Chemical reactions induced by the room temperature interaction of hyperthermal atomic hydrogen with the native oxide layer on GaAs(001) surfaces studied by ion scattering spectroscopy and X-ray photoelectron spectroscopy", <u>J. Vac. Sci. Technol.</u> , (1997), vol. 15, No. 5, pages 2502-2507	
	AL	KORZEC et al. "Characterization of a slot antenna microwave plasma source for hydrogen plasma cleaning", <u>J. Vac. Sci. Technol.</u> , (1995), vol. 13, No. 4, page 2074-2085	
	AM	EPI MBE Production Group. Aug./Sept., 1994, Applications Note, "On the Use of Atomic Hydrogen in MBE"	
	AN	Application Note, "Cracking Efficiency of the EPI Atomic Hydrogen Source", EPI, January, 1996, No. 1/96	

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\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

Substituted for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Complete if Known	
		Application Number	10/086,621
		Filing Date	March 4, 2002
		First Named Inventor	V. KAGADEI et al.
		Group Art Unit	
		Examiner Name	
Sheet 3	of 3	Attorney Docket Number	KAGADEI=1

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
	AO	LIVSHITS et al., "Dissociation of hydrogen molecules on Metal filaments in H <sup>+</sup> ion sources", <u>Plasma Source Sci. Technol.</u> , (1994), pages 465-472	
	AP	HOFLUND et al., "Performance Characteristics of a hyperthermal oxygen-atom generator", <u>Meas. Sci. Technol.</u> , (1994), vol 5, pages 201-204	
	AQ	MERFY et al., "Convenient source with a SHF-discharge in an elongated resonator for producing streams of hydrogen atoms" <u>Devices for Scientific Investigations</u> , (1979), vol. 5, Pages 121-122	XXX
	AR	GEDDES et al., "Dissociation for hydrogen in High frequency discharges", <u>Plasma Source Sci. Technol.</u> , (1993), vol. 2, pages 93-99	
	AS	RF Gas Cracker/Reactive Atom Source - HD Series, The product of Oxford Applied Research	
	AT	GOODMAN et al., "Ar, N <sub>2</sub> , and Cl <sub>2</sub> electron cyclotron resonance plasma measured by time-of-flight analysis: Neutral kinetic energies and source gas cracking", <u>J. Vac. Sci. Technol.</u> , (1997), B vol. 15, No. 4, pages 971-982	
	AU	SHERMAN, "In Situ removal of native oxide from silicon wafers", <u>J. Vac. Sci. Technol.</u> , B vol. 8, No. 4, pages 656-657	
	AV	SAMANO et al., "An arc discharge hydrogen atom source", <u>Rev. Sci. Instrum.</u> , (1993), vol. 64, No. 10, pages 2746-2752	
	AW	GOURRIER et al., "Growth of Dielectric Films of Semiconductors and Metals Using a Multipole Plasma", <u>Thin Solid Films</u> , (1981), vol. 84, Pages 379-388	
	AY	Handbook of Ion Sources, Ed. by Bernard Wolf, CRC Press, (1995), Pages 32-34, 54-56, 61, 69-71, 222-223	
	AZ	GABOVICH et al., "Out of plasma with high concentration of concentration of charged particles into vacuum", <u>Journal of Technical Physics</u> , (1961), vol. 31, No. 9, Pages 1049-1055	XXX
	BA	ITO et al., "Purification of diamond films by applying current into the plasma stream in the arc discharge plasma jet chemical vapor deposition technique", <u>J. Appl. Phys.</u> , (1995), vol. 77, No. 12, Pages 6636-6640	

Examiner Signature	Date Considered	RECEIVED
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